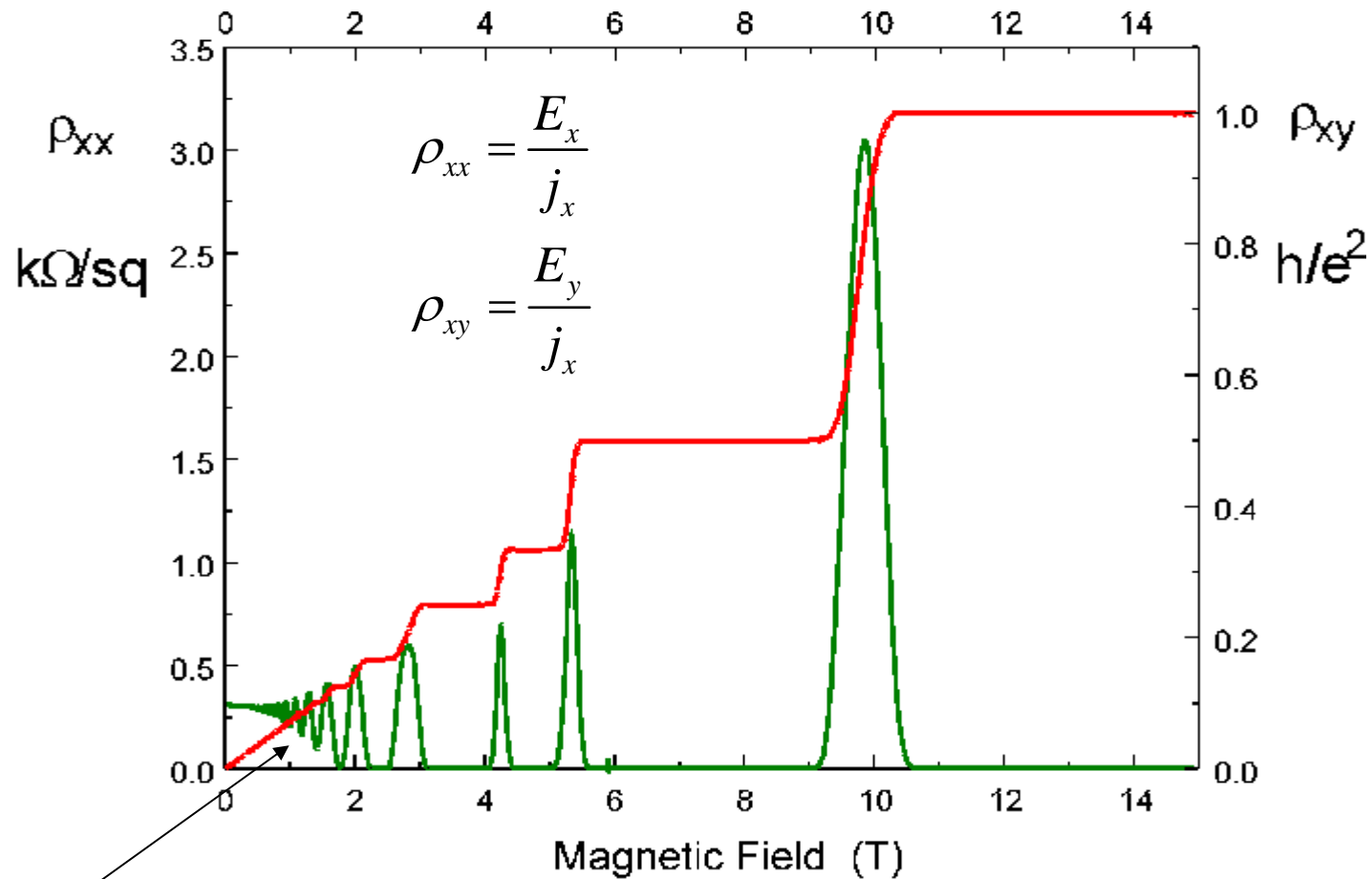


Quantum Hall Effect

Quantum Hall Effect



Klaus von Klitzing

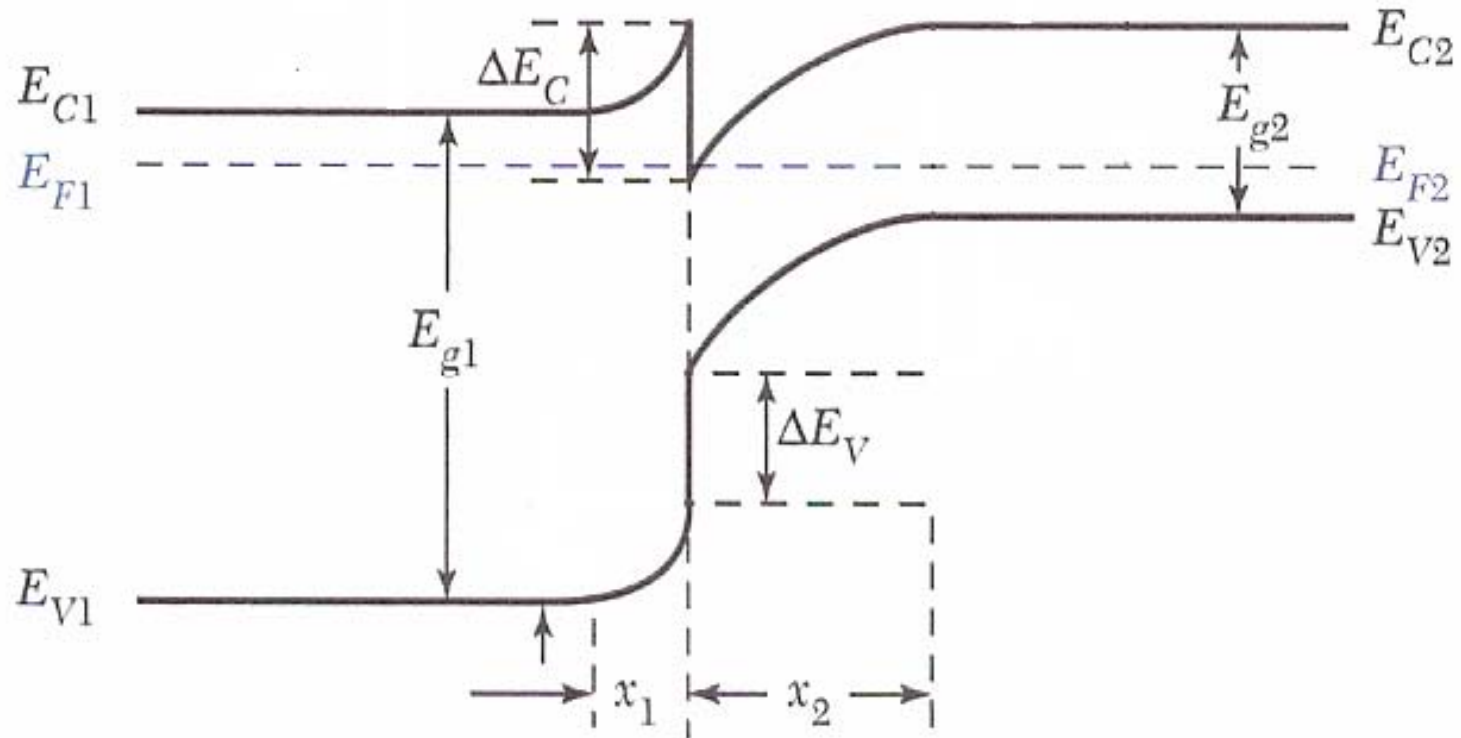


Shubnikov-De Haas oscillations

Resistance standard
25812.807557(18) Ω

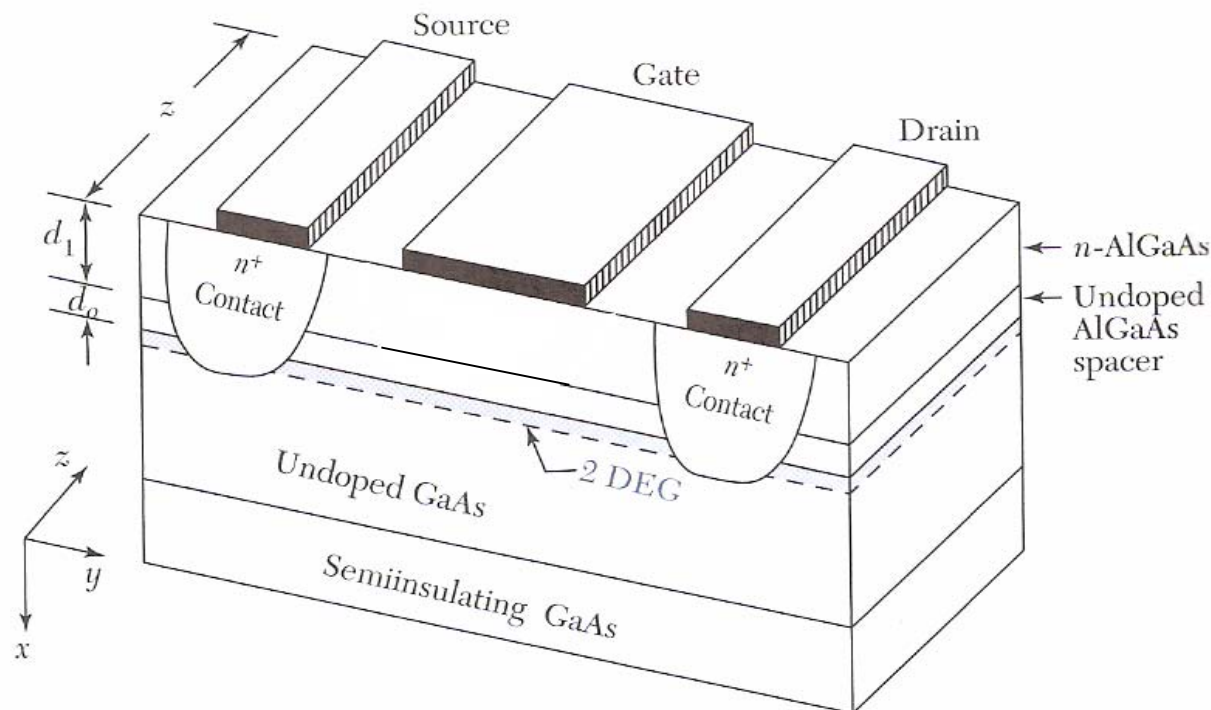
Heterostructure

pn junction formed from two semiconductors with different band gaps



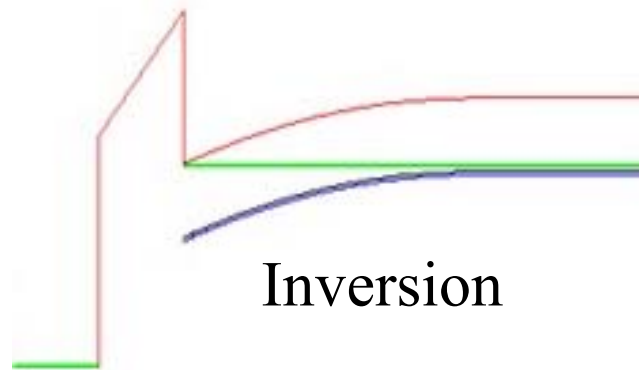
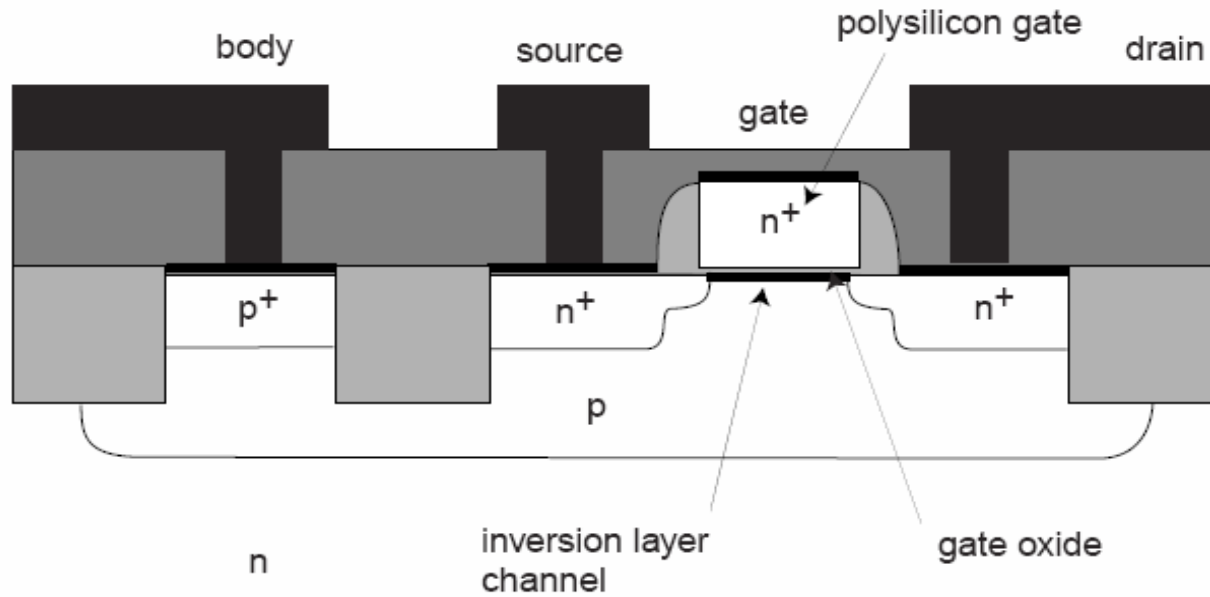
MODFET (HEMT)

Modulation doped field effect transistor (MODFET)
High electron mobility transistor (HEMT)



The magnetic field can be at an angle to the 2DEG. The Landau splitting experiences the component perpendicular to the plane. The Zeeman splitting experiences the full field.

MOSFETs



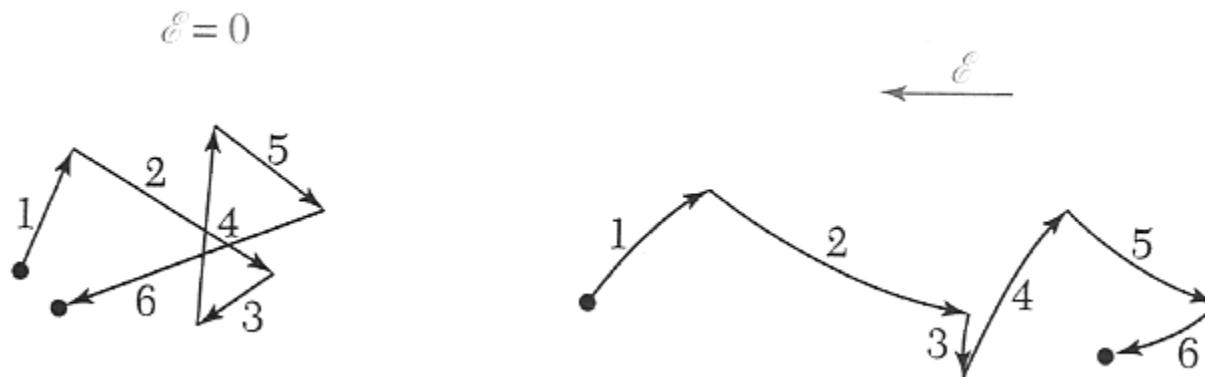
Drift

The electrons scatter and change direction after a time τ_{sc} .

Classical equipartition: $\frac{1}{2} m v_{th}^2 = \frac{3}{2} k_B T$

At 300 K, $v_{th} \sim 10^7$ cm/s.

mean free path: $\ell = v_{th} \tau_{sc} \sim 10$ nm ~ 200 atoms



Drift (diffusive transport)

$$\vec{F} = -e\vec{E} = m^* \vec{a} = m^* \frac{d\vec{v}}{dt}$$

$$\vec{v} = \vec{v}_0 - \frac{e\vec{E}}{m^*} (t - t_0)$$

$$\langle \vec{v}_0 \rangle = 0$$

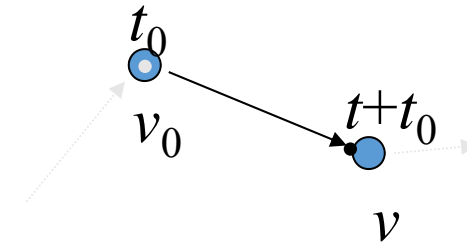
$$\langle t - t_0 \rangle = \tau_{sc}$$

$$\vec{v}_d = \frac{-e\vec{E}\tau_{sc}}{m^*} = \frac{-e\vec{E}\ell}{m^* v}$$

drift velocity: $\vec{v}_{d,n} = -\mu_n \vec{E}$

$$\vec{v}_{d,p} = \mu_p \vec{E}$$

time between two collisions



Review of the Hall effect

$$\vec{F} = m\vec{a} = -e\vec{E} = m \frac{\vec{v}_d}{\tau_{sc}} \longleftarrow \text{diffusive regime}$$

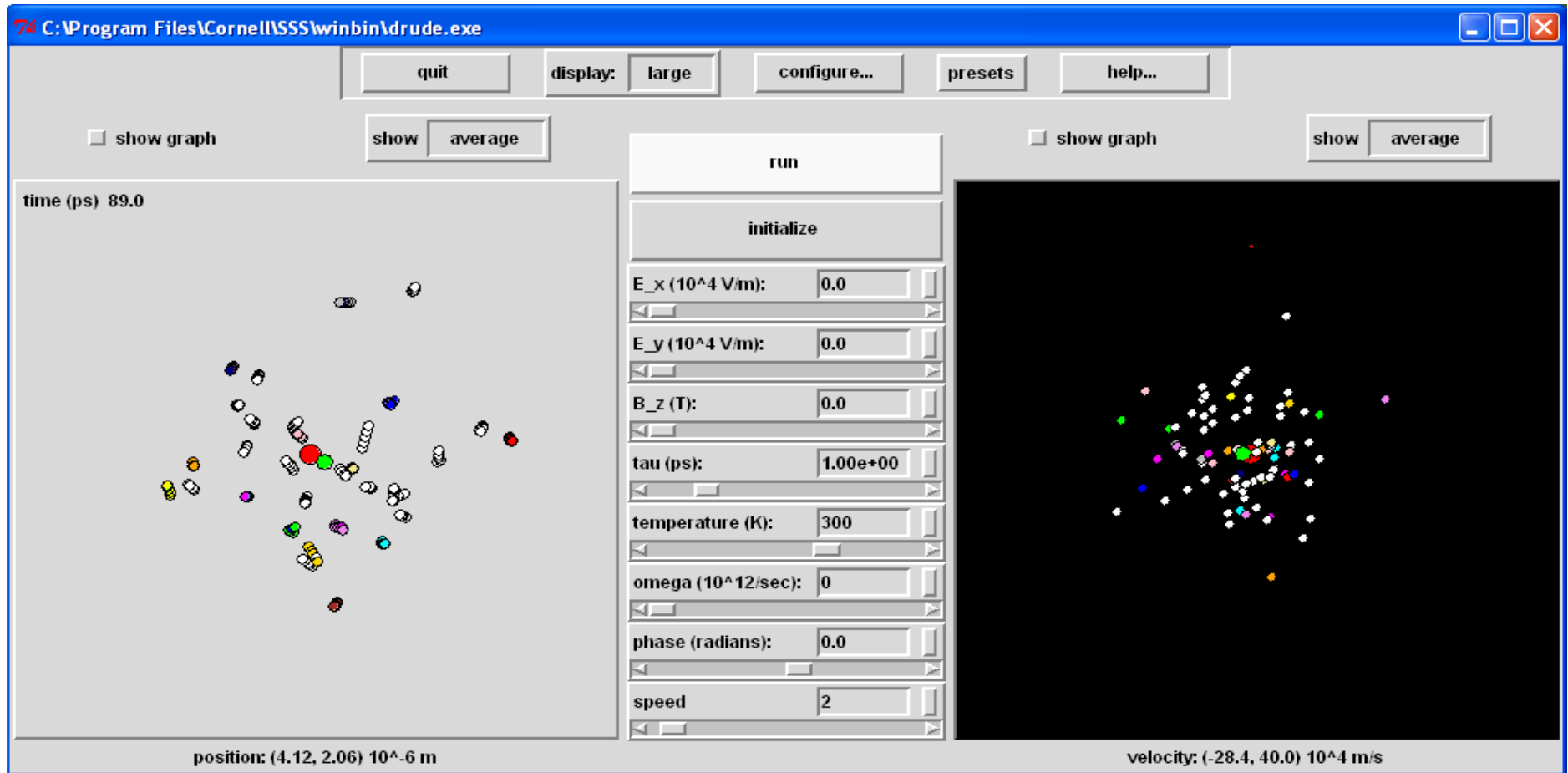
$$\vec{F} = -e(\vec{E} + \vec{v} \times \vec{B}) = m \frac{\vec{v}_d}{\tau_{sc}}$$

If B is in the z -direction, and E is in the x - direction, the three components of the force are

$$-e(E_x + v_{dy} B_z) = m \frac{v_{dx}}{\tau_{sc}}$$

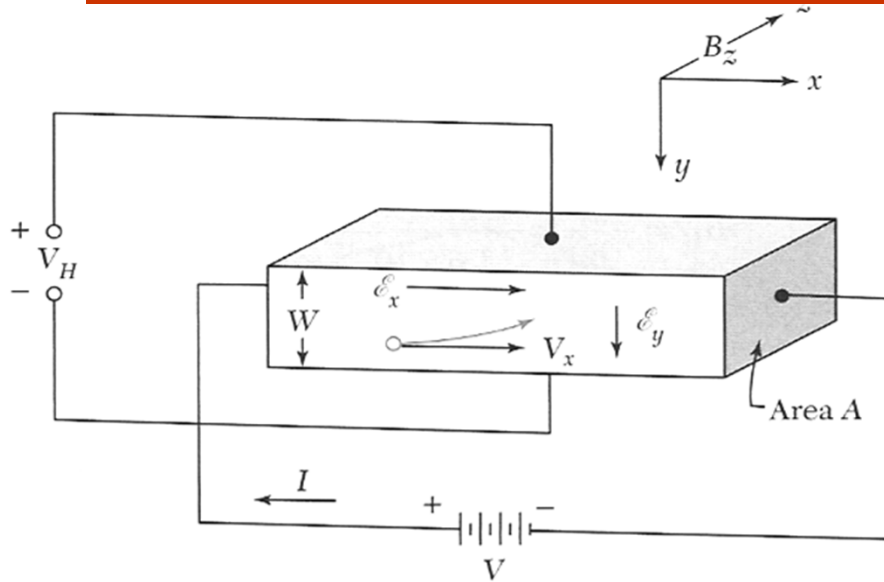
$$e v_{dx} B_z = m \frac{v_{dy}}{\tau_{sc}} \quad \Rightarrow \quad \tan \theta_H = -\frac{e B_z}{m} \tau_{sc}$$

$$0 = m \frac{v_{dz}}{\tau_{sc}} \quad \text{Hall angle}$$



If no forces are applied, the electrons diffuse.
 The average velocity moves against an electric field.
 In just a magnetic field, the average velocity is zero.
 In an electric and magnetic field, the electrons move in a straight line at the Hall angle.
 The drift velocity decreases as the B field increases.

The Hall Effect (diffusive regime)



$$v_{d,x} = -\frac{eE_x \tau_{sc}}{m} - \frac{eB_z}{m} \tau_{sc} v_{d,y}$$

$$v_{d,y} = -\frac{eE_y \tau_{sc}}{m} + \frac{eB_z}{m} \tau_{sc} v_{d,x}$$

$$v_{d,z} = -\frac{eE_z \tau_{sc}}{m}$$

If $v_{d,y} = 0$,

$$E_y = v_{d,x} B_z = V_H / W = R_H j_x B_z \quad V_H = \text{Hall voltage}, R_H = \text{Hall Constant}$$

$$v_{d,x} = -j_x / ne$$

$$R_H = E_y / j_x B_z = -1 / ne$$

The Hall Effect (diffusive regime)

$$\rho_{xx} = \frac{E_x}{j_x}$$

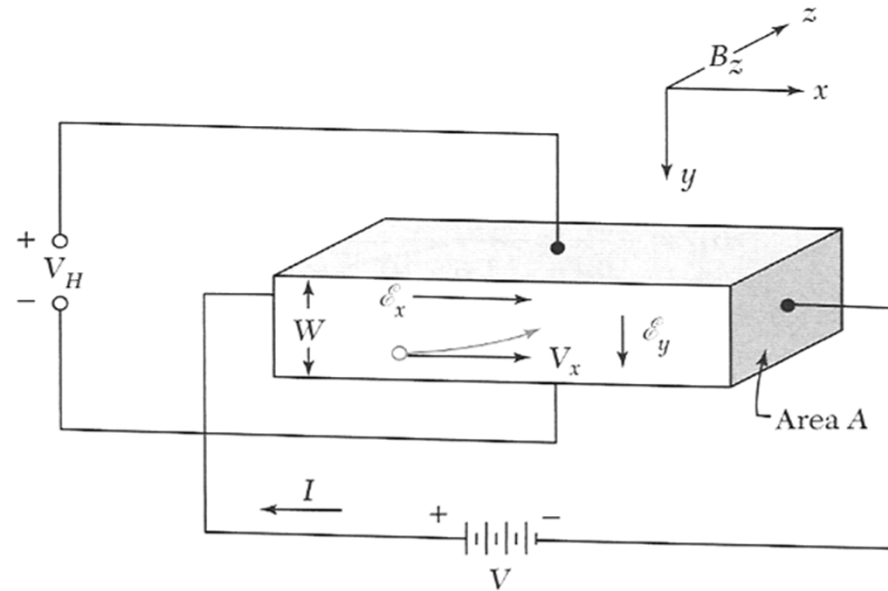
$$\rho_{xy} = \frac{E_y}{j_x}$$

$$R_H = E_y / j_x B_z = -1/ne$$

multiply both sides by B_z

$$\rho_{xy} = \frac{E_y}{j_x} = \frac{-B_z}{ne}$$

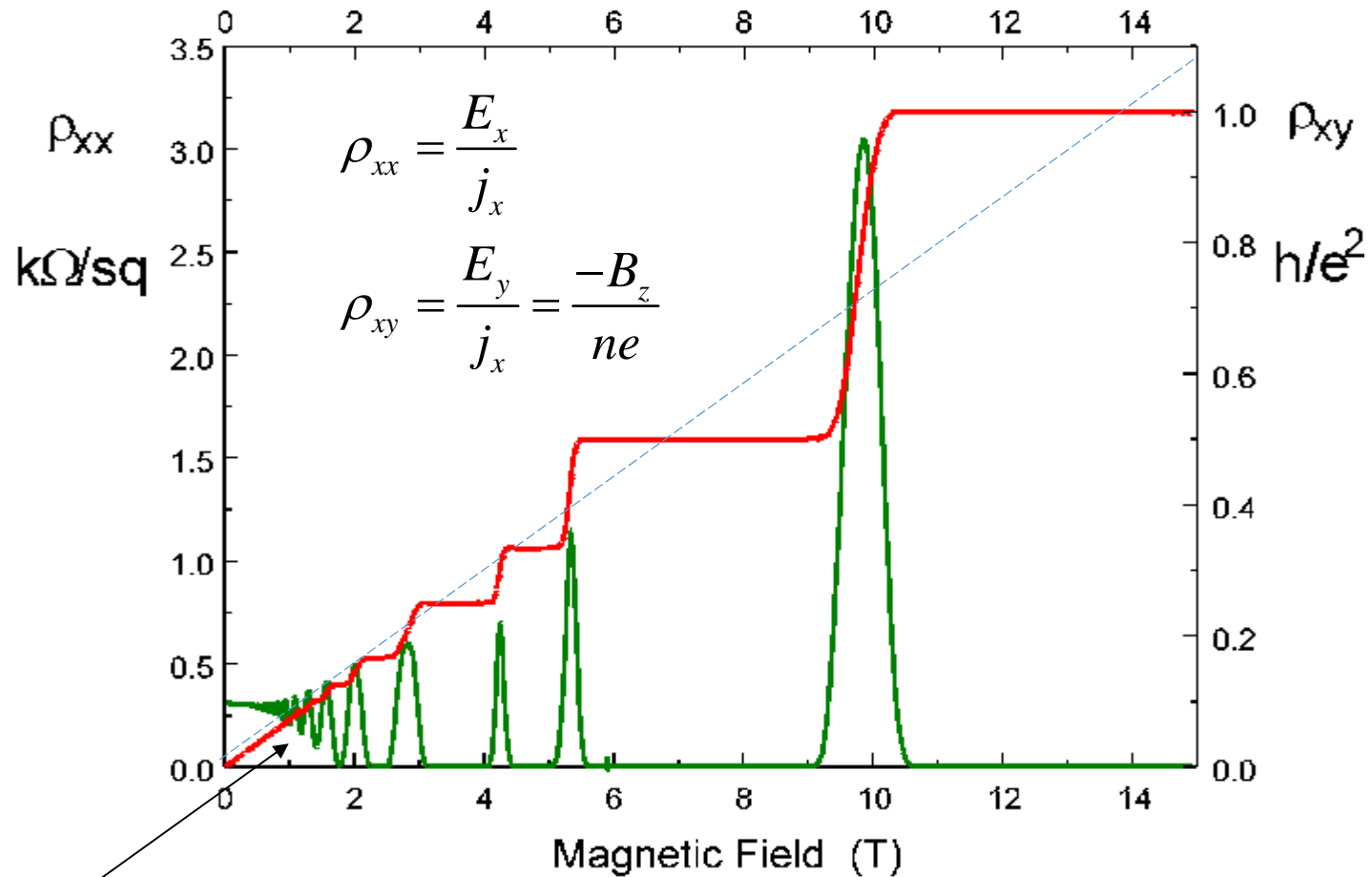
The Hall resistivity is proportional to the magnetic field.



In 2D, j has units of A/m and n has units of $1/m^2$.

In 3D, j has units of A/m^3 and n has units of $1/m^3$.

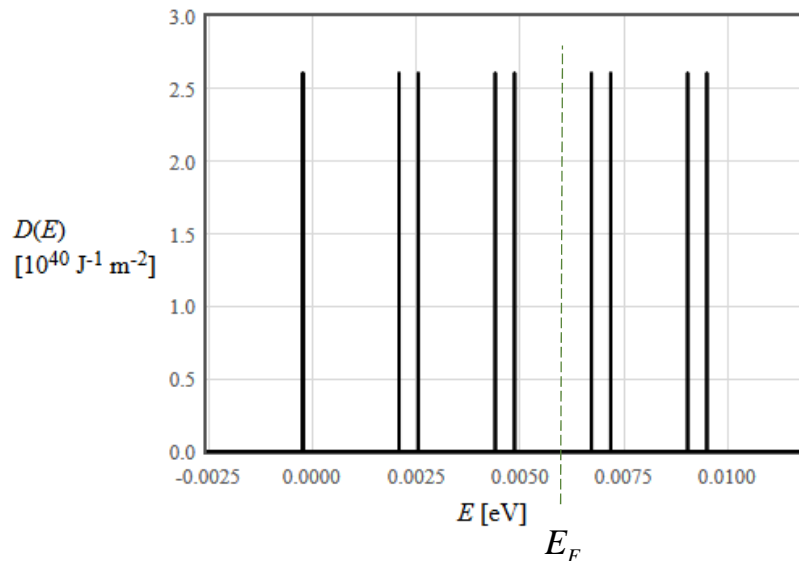
Quantum Hall Effect



Shubnikov-De Haas oscillations

Resistance standard
25812.807557(18) Ω

Quantum hall effect



If the Fermi energy is between Landau levels, the electron density n is an integer ν times the degeneracy of the Landau level $n = D_0 \nu$

$$\rho_{xy} = \frac{E_y}{j_x} = \frac{-B_z}{ne}$$

Each Landau level can hold the same number of electrons.

$$D_0 = \frac{m\omega_c}{2\pi\hbar} = \frac{eB_z}{h}$$

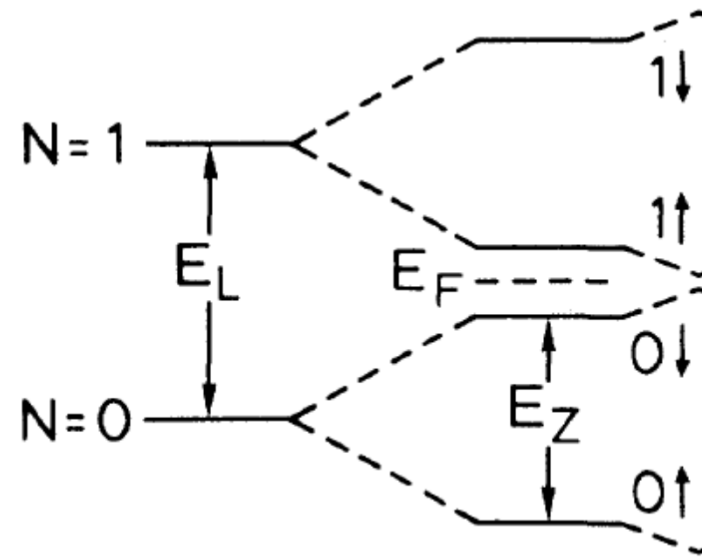
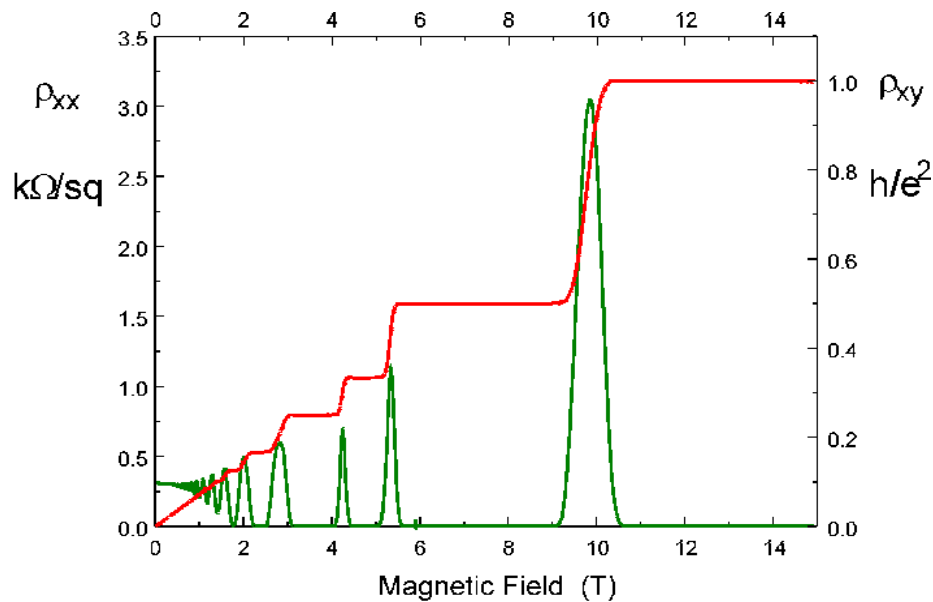
$$\rho_{xy} = \frac{-B_z}{ne} = \frac{-hD_0}{ve^2 D_0} = \frac{-h}{ve^2}$$

$$\omega_c = \frac{eB_z}{m}$$

$$B_z = \frac{hD_0}{e}$$

Quantum hall effect

$$\rho_{xy} = \frac{h}{ve^2}$$

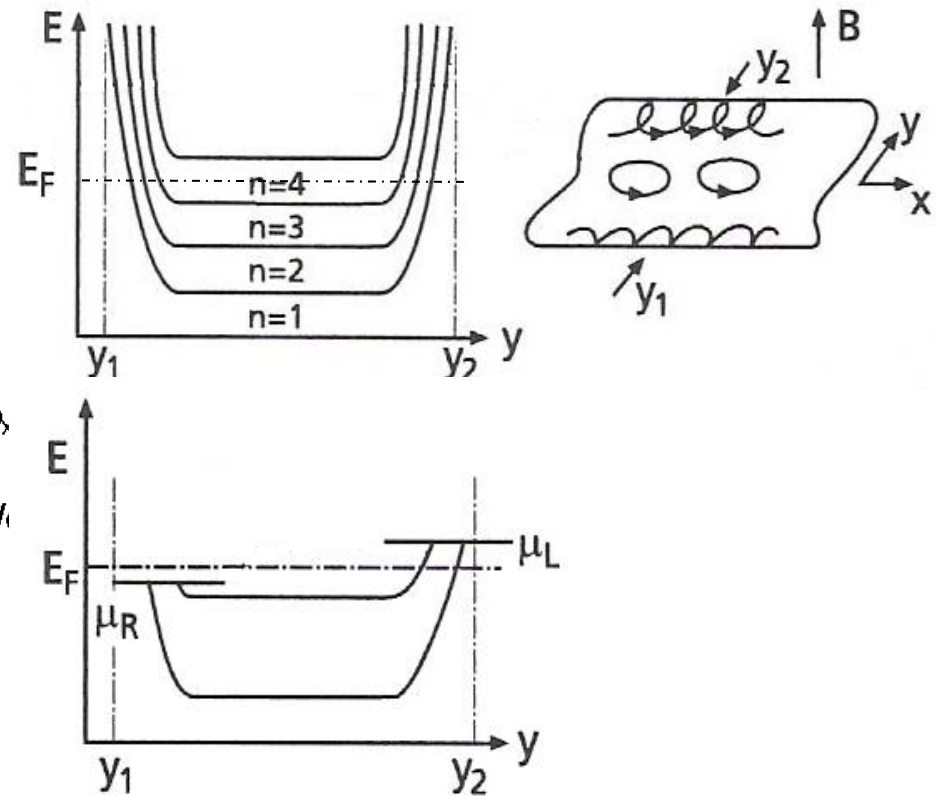
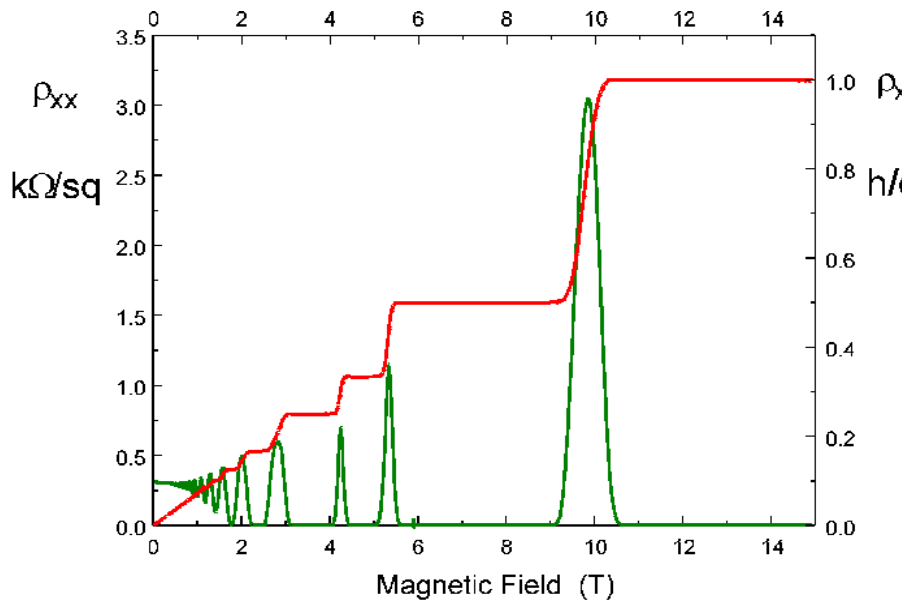


S. Koch, R. J. Haug, and K. v. Klitzing,
Phys. Rev. B 47, 4048–4051 (1993)

Quantum Hall effect

Edge states are responsible for the zero resistance in ρ_{xx}

On the plateaus, resistance goes to zero because there are no states to scatter into.



Ibach & Lueth (modified)